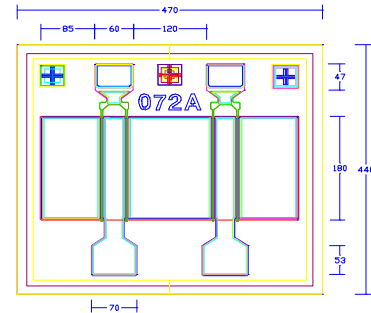


**PRELIMINARY DATA SHEET**
**Low Distortion GaAs Power FET**

- +25.0dBm TYPICAL OUTPUT POWER
- 10.0dB TYPICAL POWER GAIN AT 12GHz
- 0.3 X 720 MICRON RECESSED “MUSHROOM” GATE
- Si<sub>3</sub>N<sub>4</sub> PASSIVATION
- ADVANCED EPITAXIAL DOPING PROFILE PROVIDES HIGH POWER EFFICIENCY, LINEARITY AND RELIABILITY
- Idss SORTED IN 15mA PER BIN RANGE



Chip Thickness: 75 ± 13 microns  
All Dimensions In Microns

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)**

SYMBOLS	PARAMETERS/TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>P<sub>1dB</sub></b>	Output Power at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>dss</sub>	22.5	25.0 25.0		dBm
<b>G<sub>1dB</sub></b>	Gain at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>dss</sub>	8.0	10.0 7.5		dB
<b>PAE</b>	Power Added Efficiency at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>dss</sub>		32		%
<b>I<sub>dss</sub></b>	Saturated Drain Current V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	120	190	270	mA
<b>G<sub>m</sub></b>	Transconductance V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	80	110		mS
<b>V<sub>p</sub></b>	Pinch-off Voltage V <sub>ds</sub> =3V, I <sub>ds</sub> =2.0mA		-2.0	-3.5	V
<b>BV<sub>gd</sub></b>	Drain Breakdown Voltage I <sub>gd</sub> =1.0mA	-12	-15		V
<b>BV<sub>gs</sub></b>	Source Breakdown Voltage I <sub>gs</sub> =1.0mA	-7	-14		V
<b>R<sub>th</sub></b>	Thermal Resistance (Au-Sn Eutectic Attach)		55		°C/W

**MAXIMUM RATINGS AT 25°C**

SYMBOLS	PARAMETERS	ABSOLUTE <sup>1</sup>	CONTINUOUS <sup>2</sup>
<b>V<sub>ds</sub></b>	Drain-Source Voltage	12V	8V
<b>V<sub>gs</sub></b>	Gate-Source Voltage	-8V	-4V
<b>I<sub>ds</sub></b>	Drain Current	I <sub>dss</sub>	260Ma
<b>I<sub>gsf</sub></b>	Forward Gate Current	20mA	4mA
<b>P<sub>in</sub></b>	Input Power	25dBm	@ 3dB Compression
<b>T<sub>ch</sub></b>	Channel Temperature	175°C	150°C
<b>T<sub>stg</sub></b>	Storage Temperature	-65/175°C	-65/150°C
<b>P<sub>t</sub></b>	Total Power Dissipation	2.5 W	2.1 W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

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# EFA072A

## PRELIMINARY DATA SHEET

### Low Distortion GaAs Power FE

#### S-PARAMETERS

6V, 100 mA

#### S-PARAMETERS

8V, 1/2Idss

FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---		FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.975	-29.2	7.010	158.8	0.020	73.8	0.387	-18.9	1.0	0.972	-29.7	7.064	158.3	0.021	73.2	0.452	-17.3
2.0	0.933	-55.6	6.350	140.9	0.037	59.8	0.365	-37.6	2.0	0.931	-56.4	6.382	140.1	0.037	59.1	0.425	-33.8
3.0	0.899	-77.3	5.596	126.0	0.049	48.7	0.357	-52.5	3.0	0.896	-78.4	5.605	124.8	0.048	48.3	0.410	-47.2
4.0	0.862	-95.5	4.962	114.2	0.057	41.2	0.379	-61.2	4.0	0.858	-96.7	4.934	112.8	0.055	40.4	0.425	-55.4
5.0	0.844	-106.9	4.290	104.2	0.061	35.9	0.346	-68.4	5.0	0.842	-108.0	4.273	102.8	0.059	34.9	0.394	-61.9
6.0	0.822	-120.9	3.774	93.1	0.064	29.0	0.331	-83.0	6.0	0.820	-121.9	3.754	91.5	0.060	28.5	0.373	-75.1
7.0	0.802	-132.2	3.402	85.0	0.065	25.4	0.351	-86.5	7.0	0.802	-133.1	3.377	83.2	0.062	24.6	0.392	-78.9
8.0	0.805	-136.0	3.083	79.0	0.066	23.5	0.328	-90.0	8.0	0.805	-136.8	3.059	77.3	0.063	23.8	0.371	-81.9
9.0	0.805	-141.5	2.754	71.6	0.066	20.6	0.310	-102.9	9.0	0.804	-142.3	2.738	69.9	0.062	20.0	0.350	-93.8
10.0	0.797	-149.6	2.504	64.3	0.064	17.6	0.328	-110.6	10.0	0.799	-150.2	2.483	62.4	0.061	17.3	0.366	-102.0
11.0	0.802	-154.5	2.296	58.2	0.064	17.1	0.333	-117.5	11.0	0.803	-155.2	2.286	55.9	0.061	16.9	0.369	-108.6
12.0	0.802	-160.8	2.097	51.5	0.064	15.7	0.356	-125.0	12.0	0.803	-161.4	2.079	49.1	0.059	14.9	0.391	-116.3
13.0	0.803	-166.1	1.963	45.9	0.064	14.2	0.368	-127.2	13.0	0.805	-166.7	1.943	43.4	0.059	14.4	0.405	-119.2
14.0	0.813	-167.4	1.805	40.8	0.062	15.0	0.374	-137.6	14.0	0.816	-167.9	1.791	38.1	0.059	15.2	0.408	-129.4
15.0	0.828	-175.8	1.581	33.5	0.059	11.8	0.438	-143.2	15.0	0.832	-176.3	1.564	30.4	0.055	14.4	0.471	-136.1
16.0	0.834	171.5	1.508	27.3	0.060	11.4	0.472	-133.5	16.0	0.837	171.1	1.482	23.9	0.056	12.6	0.510	-127.7
17.0	0.819	177.2	1.514	24.7	0.066	14.1	0.439	-141.8	17.0	0.823	176.7	1.491	21.4	0.061	15.2	0.479	-135.6
18.0	0.833	176.8	1.311	20.0	0.062	15.5	0.495	-154.0	18.0	0.836	176.6	1.293	16.4	0.058	15.9	0.530	-148.1
19.0	0.832	160.7	1.194	13.2	0.061	13.5	0.550	-143.2	19.0	0.835	160.3	1.167	9.5	0.058	15.4	0.587	-138.7
20.0	0.824	156.5	1.151	8.4	0.065	13.3	0.564	-143.6	20.0	0.827	156.2	1.121	4.6	0.060	16.0	0.605	-139.5
21.0	0.834	155.4	1.223	4.4	0.077	14.3	0.508	-148.1	21.0	0.837	154.9	1.197	0.5	0.070	18.2	0.549	-143.6
22.0	0.821	162.6	1.109	1.4	0.075	16.7	0.554	-163.5	22.0	0.825	162.2	1.088	-2.7	0.071	20.4	0.595	-158.9
23.0	0.833	154.1	1.012	-4.1	0.075	17.6	0.578	-161.8	23.0	0.837	153.9	0.986	-8.4	0.071	20.2	0.622	-158.1
24.0	0.832	149.9	1.017	-9.0	0.083	16.3	0.571	-165.5	24.0	0.836	149.3	0.991	-13.5	0.080	20.0	0.615	-161.4
25.0	0.831	151.9	0.939	-12.6	0.086	17.9	0.602	-175.8	25.0	0.837	151.2	0.921	-17.9	0.084	20.7	0.649	-172.1
26.0	0.834	144.0	0.899	-18.7	0.090	16.8	0.611	-175.8	26.0	0.842	143.3	0.867	-23.9	0.088	20.8	0.656	-172.4

Note: The data included 0.7 mils diameter Au bonding wires:  
2 gate wires, 15 mils each; 2 drain wires, 20 mils each; 6 source wires, 10 mils each.